

General Description

The CMB029N10-7 uses advanced SGT technology to provide excellent $R_{DS(ON)}$.

This technology has been optimized to minimize on-state resistance and yet maintain superior switching performance.

Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

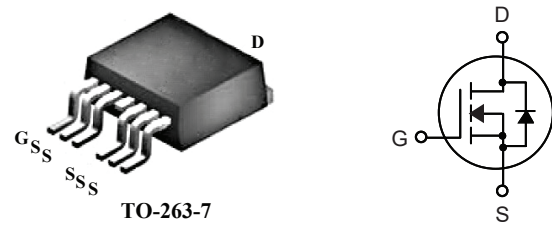
Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
100V	2.3mΩ	200A

Applications

- DC Motor Drive
- Uninterruptible Power Supply
- High Speed Power Switching

TO-263-7 Pin Configuration



Type	Package	Marking
CMB029N10-7	TO-263-7	CMB029N10-7

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current	200	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current	140	A
I_{DM}	Pulsed Drain Current	800	A
EAS	Single Pulse Avalanche Energy ¹	4622	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	400	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient(min. footprint)	---	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-case	---	0.31	°C/W

Electrical Characteristics($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=100A$	---	1.9	2.3	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=100V$, $V_{GS}=0V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=20A$	---	55	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2	---	Ω
Q_g	Total Gate Charge	$I_D=90A$ $V_{DS}=50V$ $V_{GS}=10V$	---	169	---	nC
Q_{gs}	Gate-Source Charge		---	67	---	
Q_{gd}	Gate-Drain Charge		---	30	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V$ $R_G=3\Omega$ $V_{GS}=10V$	---	35	---	ns
T_r	Rise Time		---	111	---	
$T_{d(off)}$	Turn-Off Delay Time		---	84	---	
T_f	Fall Time		---	112	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	14300	---	pF
C_{oss}	Output Capacitance		---	4700	---	
C_{rss}	Reverse Transfer Capacitance		---	370	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	200	A
I_{SM}	Pulsed Source Current		---	---	800	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=100A$, $T_J=25^{\circ}\text{C}$	---	0.86	1.4	V
t_{rr}	Reverse Recovery Time	$di/dt = 100A/\mu s$	---	101	---	ns
Q_{rr}	Reverse Recovery Charge	$T_J = 25^{\circ}\text{C}$, $I_F = 90A$	---	338	---	nC

Note :

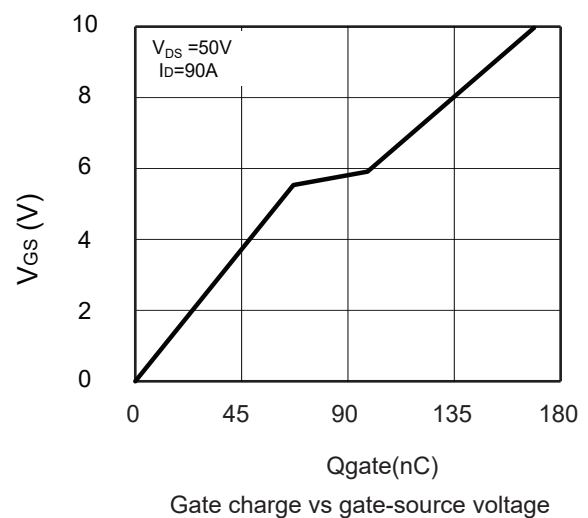
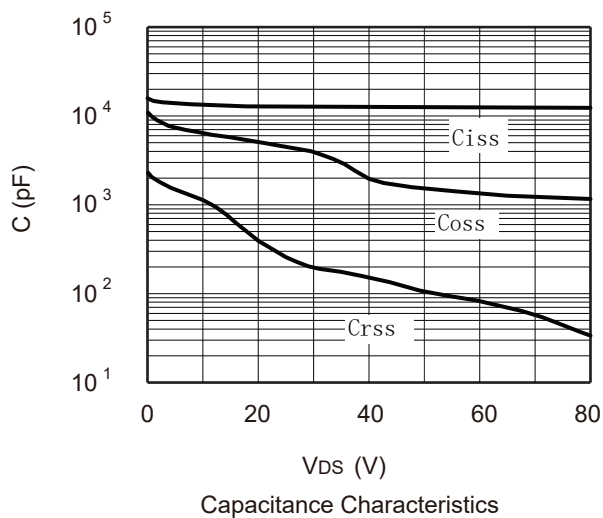
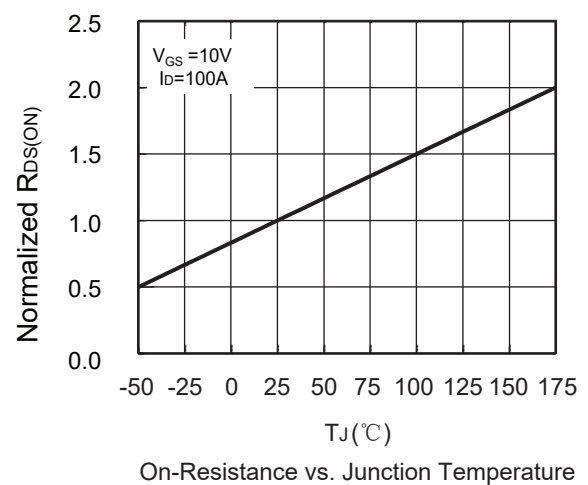
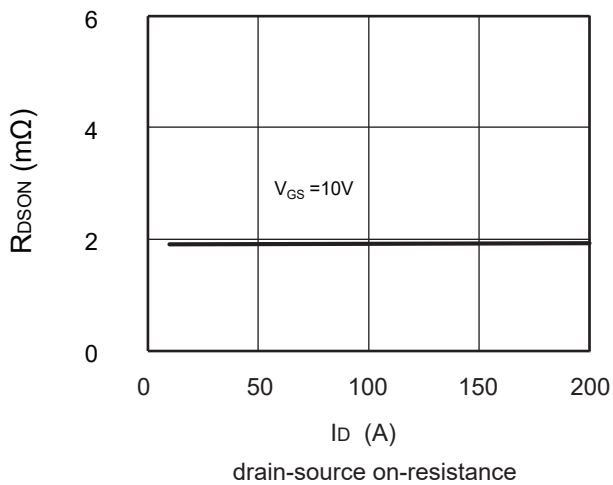
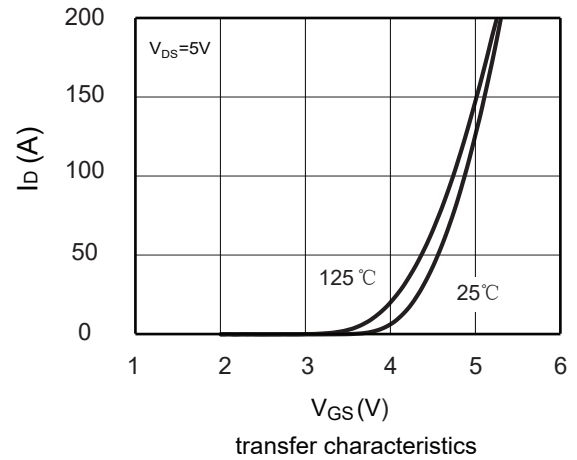
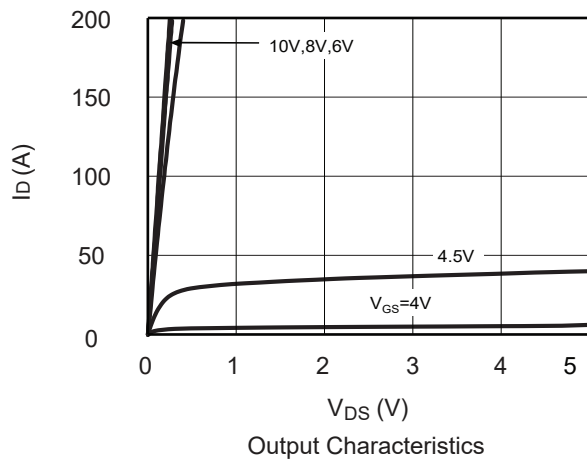
1.The EAS data shows Max. rating . The test condition is $V_{DD}=100V$, $V_{GS}=10V$, $L=5\text{mH}$, $I_{AS}=43A$.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design, functions and reliability without notice. Please refer to the latest version of specification.

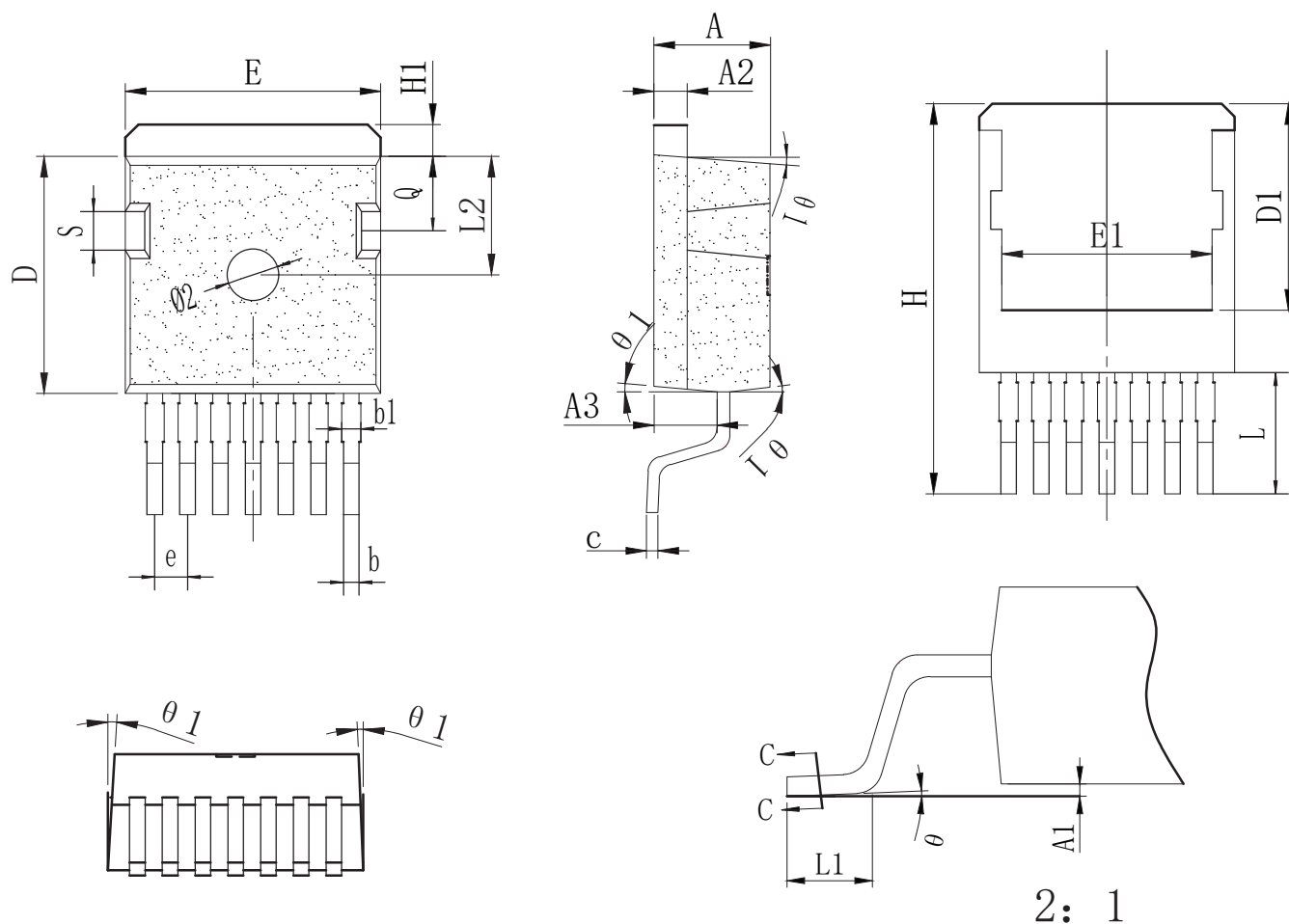
Typical Characteristics



Package Dimension

TO-263-7

Unit :mm



SYMBOL	mm			SYMBOL	mm		
	MIN	NOM	MAX		MIN	NOM	MAX
*A	4.30	4.40	4.50	E1	8.20	8.40	8.60
*A1	0.00	0.10	0.20	*e	1.25	1.27	1.29
*A2	1.22	1.27	1.32	*H	14.85	15.00	15.15
*A3	2.30	2.40	2.50	H1	1.10	1.20	1.30
*b	0.50	0.60	0.70	*L	4.50	4.70	4.90
*b1	—	—	0.63	L1	1.70	2.00	2.30
*c	0.45	0.50	0.55	L2	4.55	4.65	4.75
*D	9.15	9.30	9.45	S	1.40	1.50	1.60
D1	规格A: 8.00REF			Q	2.80	2.90	3.00
	规格B: 5.70REF			* θ	0°	2.5°	8°
*E	10.12	10.16	10.20	θ_1	5°	7°	9°